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SPECIFICATION

Kindly amend the following paragraph, at page 15, lines 2-9, to read as follows:

In the next step of the process in accordance with one embodiment of the present invention, shown schematically in Fig. 12 as step 1203, a nitrogen-containing charge trapping dielectric charge storage layer 24 is formed on the bottom oxide layer 22. In one ~~embodiment~~ embodiment, the charge storage layer 24 comprises a nitride, and in one embodiment, the nitride is silicon nitride. The nitrogen-containing charge storage layer 24 includes a form of nitrogen capable of migrating under annealing conditions from the charge storage layer 24 into the bottom oxide layer 22. A schematic illustration of the structure formed by this step is depicted in Fig. 6.

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